

**Journal of**

**Materials Chemistry C**

COMMUNICATION

Supplementary information

**Photolithographic stretchable transparent electrode for all-solution-processed fully transparent conformal organic transistor array†**

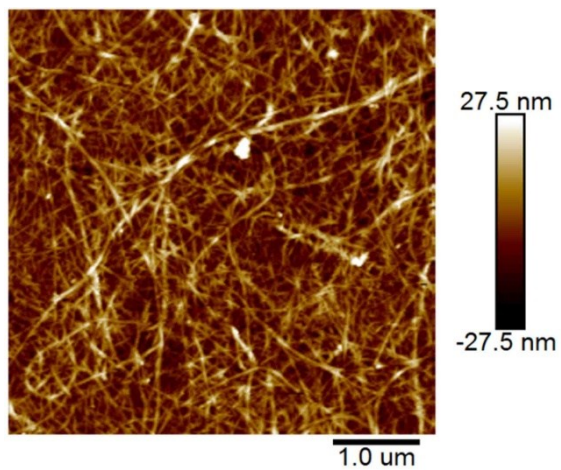
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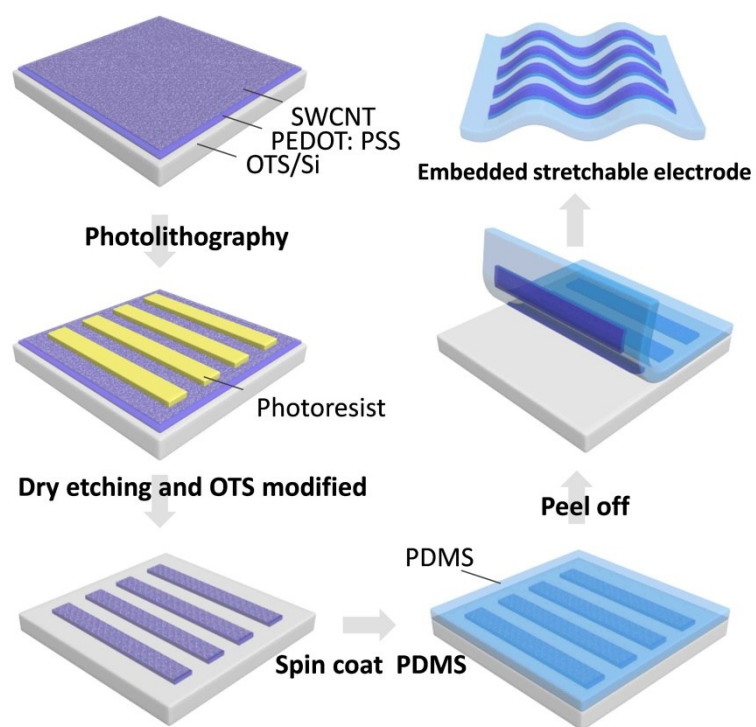
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**S1. Morphology of SWCNT network on PEDOT:PSS thin film.**



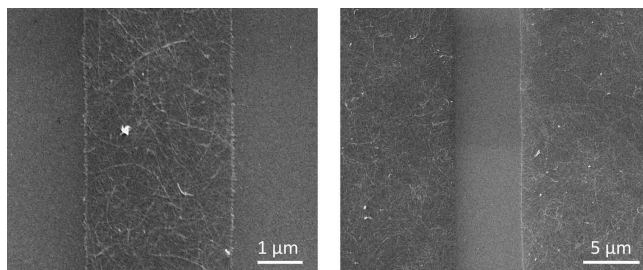
**Fig. S1** AFM image of dense SWCNT network on PEDOT:PSS thin film.

**S2. Fabrication process of photolithographic stretchable transparent PEDOT:PSS/SWCNT hybrid electrode.**



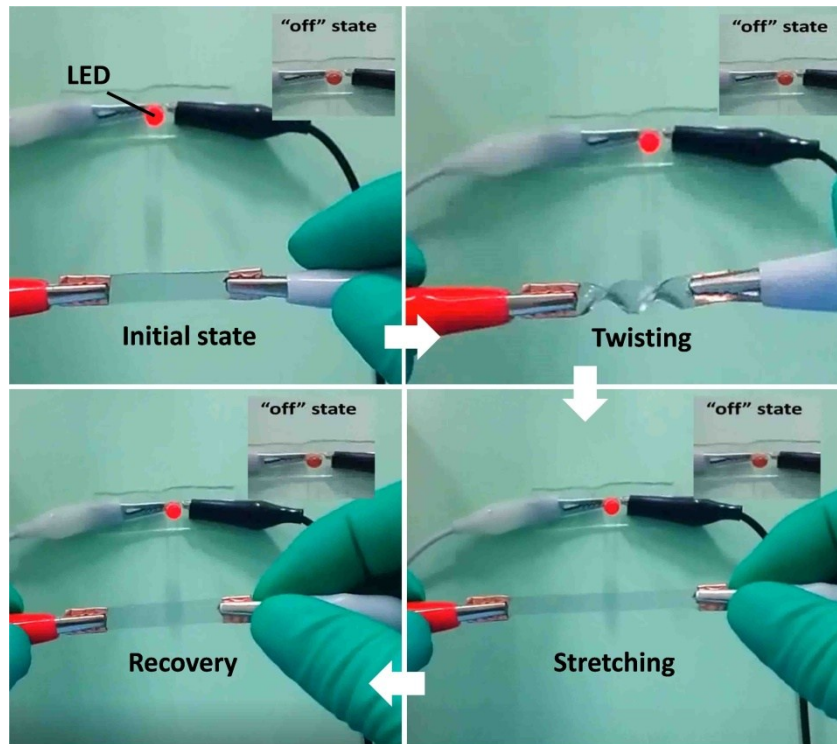
**Fig. S2** Schematic illustration for the fabrication process of photolithographic stretchable transparent PEDOT:PSS/SWCNT hybrid electrode.

### S3. Morphology of photolithographic PEDOT:PSS/SWCNT patterns.

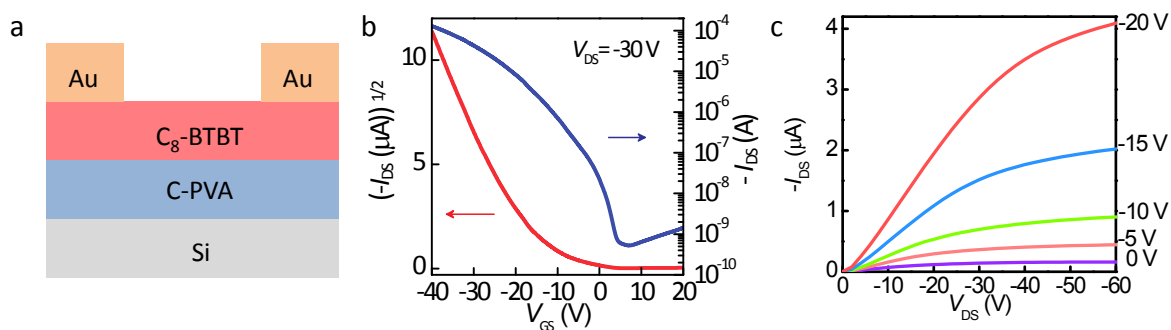


**Fig. S3** SEM images of PEDOT:PSS/SWCNT patterns.

#### S4. Deformability of the PEDOT:PSS/SWCNT electrode.



## S5. OTFT devices fabricated by conventional method.



**Fig. S5** (a) Schematic image of C<sub>8</sub>-BTBT OTFT fabricated on silicon substrate (gate) with thermally evaporated Au source/drain electrode through a shadow mask. (b,c) Typical transfer and output characteristics of the device measured in air at room temperature. ( $\mu = 1.7\text{ cm}^2\text{ V}^{-1}\text{ s}^{-1}$ )

## S6. Performances of reported flexible OTFTs and our transparent conformal OTFTs with PEDOT:PSS/SWCNT electrode.

Table S6. Performances of reported flexible OTFTs and our transparent conformal OTFTs.

Semiconductor	Electrode	Dielectric	$\mu$ (cm <sup>2</sup> V <sup>-1</sup> s <sup>-1</sup> )	V <sub>T</sub> (V)	I <sub>on</sub> /I <sub>off</sub>	Ref.
DPh-DNTT pentacene	Au (source/drain); Al (gate)	AlO <sub>x</sub> /SAM	2.0	2 V	>10 <sup>5</sup>	[1]
DNTT PTAA	Au (source/drain); Ag (gate)	parylene-C	0.37	-21.3	4.9 × 10 <sup>5</sup>	[2]
			0.36	-15.7	1.6 × 10 <sup>5</sup>	
TIPS pentacene	PEDOT:PSS (source/drain); Ag (gate)	PVP	0.013	-13.0	6.9 × 10 <sup>4</sup>	[3]
P3HT	Au (source/drain); PEDOT:PSS (gate)	polyelectrolyte	0.95 ± 0.12	-0.19 ± 0.03	2.5 × 10 <sup>3</sup>	[4]
BTBT-C <sub>12</sub> -PA	Au (source/drain); Al (gate)	AlO <sub>x</sub>	2.0	0.5-1.0	10 <sup>5</sup>	[5]
TIPS pentacene		Mylar	1.7 × 10 <sup>-3</sup>	-	10 <sup>2</sup>	[6]
TES-ADT	Ag (source/drain/gate)	membrane	0.15	-	10 <sup>3</sup> - 10 <sup>4</sup>	
PDPP5T	Au (source/drain); Cr/Au (gate)	Al <sub>2</sub> O <sub>3</sub>	0.4	-	10 <sup>3</sup> - 10 <sup>4</sup>	[7]
PIDT-BT			0.62	-	2.47 × 10 <sup>6</sup>	[8]
P3HT	Au (source/drain/gate)	PEG	0.56	-0.35	>10 <sup>4</sup>	
N2200			1.28	0.11	>10 <sup>3</sup>	[9]
pBTTT	Au (source/drain/gate)	PMMA	0.1	-	10 <sup>2</sup>	[10]
C8-BTBT	Au (source/drain); Au grid (gate)	C-PVA	0.3	-	10 <sup>5</sup>	
pentacene			2.0	-15	10 <sup>5</sup> - 10 <sup>6</sup>	[11]
PDI-C8	Au (source/drain/gate)	PAN/PS	0.52	-8.6	-	
PTDPPSe-SiC4	Graphene/Au (source/drain); Au (gate)	SU-8	0.23	8.5	-	[12]
			1.43	-	>10 <sup>5</sup>	
C8-BTBT	PEDOT:PSS/SWCNT (source/drain/gate)	C-PVA	0.37	-	>10 <sup>2</sup>	Our work
			2.7	±10	>10 <sup>4</sup>	

[1] T. Yokota, K. Kuribara, T. Tokuhara, U. Zschieschang, H. Klauk, K. Takimiya, Y. Sadamitsu, M. Hamada, T. Sekitani and T. Someya, *Adv. Mater.*, 2013, **25**, 3639.

[2] H. Jeong, S. Baek, S. Han, H. Jang, S. H. Kim and H. S. Lee, *Adv. Funct. Mater.*, 2018, **28**, 1704433.

[3] S. Conti, S. Lai, P. Cosseddu and A. Bonfiglio, *Adv. Mater. Technol.*, 2016, 1600212.

[4] S. W. Lee, H. J. Lee, J. H. Choi, W. G. Koh, J. M. Myoung, J. H. Hur, J. J. Park, J. H. Cho and U. Jeong, *Nano Lett.*, 2010, **10**, 347.

[5] T. Schmaltz, A. Y. Amin, A. Khassanov, T. Meyer-Friedrichsen, H.-G. Steinrück, A. Magerl, J. J. Segura, K. Voitkovsky, F. Stellacci and M. Halik, *Adv. Mater.*, 2013, **25**, 4511.

[6] H. T. Yi, M. M. Payne, J. E. Anthony and V. Podzorov, *Nat. Commun.*, 2012, **3**, 1259.

[7] Y. Ding, C. Zhu, J. Liu, Y. Duan, Z. Yi, J. Xiao, S. Wang, Y. Huang and Z. g Yin, *Nanoscale*, 2017, **9**, 19050.

[8] Z. Liu, Z. Yin, J. Wang and Q. Zheng, *Adv. Funct. Mater.*, 2018, 1806092.

[9] Y. Hu, C. Warwick, A. Sou, L. Jiang and H. Sirringhaus, *J. Mater. Chem. C*, 2014, **2**, 1260.

[10] N. Cui, H. Ren, Q. Tang, X. Zhao, Y. Tong, W. Hu and Y. Liu, *Nanoscale*, 2018, **10**, 3613.

[11] L. Zhang, H. Wang, Y. Zhao, Y. Guo, W. Hu, G. Yu and Y. Liu, *Adv. Mater.*, 2013, **25**, 5455.

[12] E. K. Lee, C. H. Park, J. Lee, H. R. Lee, C. Yang and J. H. Oh, *Adv. Mater.*, 2017, **29**, 1605282.